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(54) Title: EMBOSSED PRINTING FOR FABRICATION OF ORGANIC FIELD EFFECT TRANSISTORS AND ITS INTEGRATED DEVICES

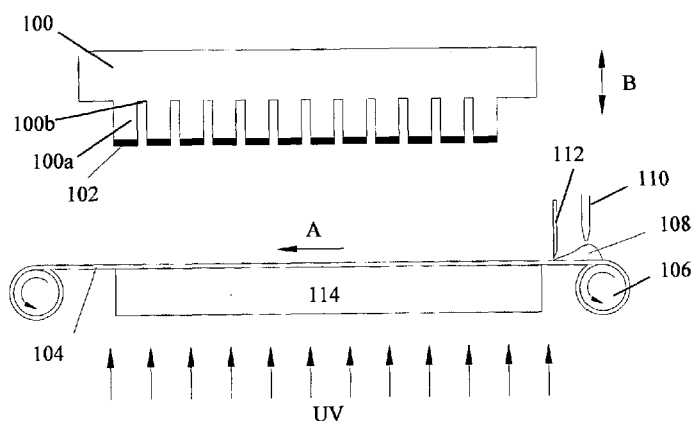


FIGURE 1

(57) Abstract: A method of fabricating an organic field effect transistor (OFET) comprises forming at least one OFET structure by ultraviolet (UV) transfer embossing printing. In an example embodiment, the method includes providing ink material (102) on at least part of a patterned surface (100a, 100b) of a mold (100). The mold (100) is then contacted on a coating of ultraviolet (UV) curable resin (108) on a substrate (104) so as to insert at least part of the ink material (102) into the resin (108). The resin (108) is then irradiated with UV light, and the mold (100) is separated from the resin (108) so as to transfer the ink material (102) onto the substrate (104) to form at least one OFET structure.